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Substitute for form 1449A/PTO			Complete If Known		
			Application Number	Not Yet Assigned 10/787,102/	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Filing Date	March 1, 2004	
			First Named Inventor	John T. Moore	
			Art Unit	Not Yet Assigned	
			Examiner Name	Not Yet Assigned	
			Attorney Docket Number	M4065.0564/P564-A	
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U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
W	AA	5,781,115	06/02/1998	Kozicki et al. **	
	AB	6,084,796	07/04/2000	Kozicki et al. **	
	AC	5,914,893	06/22/1999	Kozicki et al. **	
	AD	5,896,312	04/20/1999	Kozicki et al. **	
	AE	6,388,324	05/14/2002	Kozicki et al. **	
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	AG	5,500,532	03/19/1996	Kozicki et al. **	
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	AL	US 2002/0168820	11/14/2002	Kozicki et al. **	
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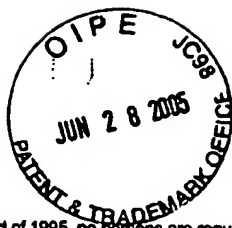
FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)			
W	BA	WO 02/21542	03/14/2002	Kozicki et al. **	
W	BB	WO 00/48196	08/17/2000	Kozicki et al. **	
W	BC	WO 97/48032	12/18/1997	Kozicki et al. **	
W	BD	WO 98/28914	06/10/1999	Kozicki et al. **	

Examiner Signature	H. Jay T. H.	Date Considered	8/2/05
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¹ Applicant's unique citation designation number (optional). ² See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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			Group Art Unit	Not Yet Assigned
			Examiner Name	Not Yet Assigned
			Attorney Docket Number	M4065.0564/P564-A
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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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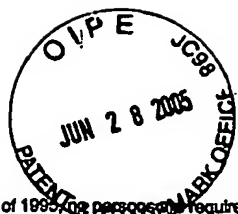
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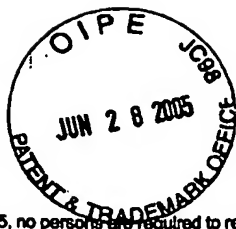
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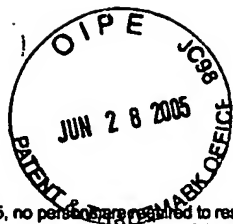
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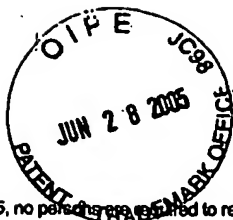
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Application Number	Not Yet Assigned 10/787/101
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Group Art Unit	Not Yet Assigned
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